



1

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1

IDM

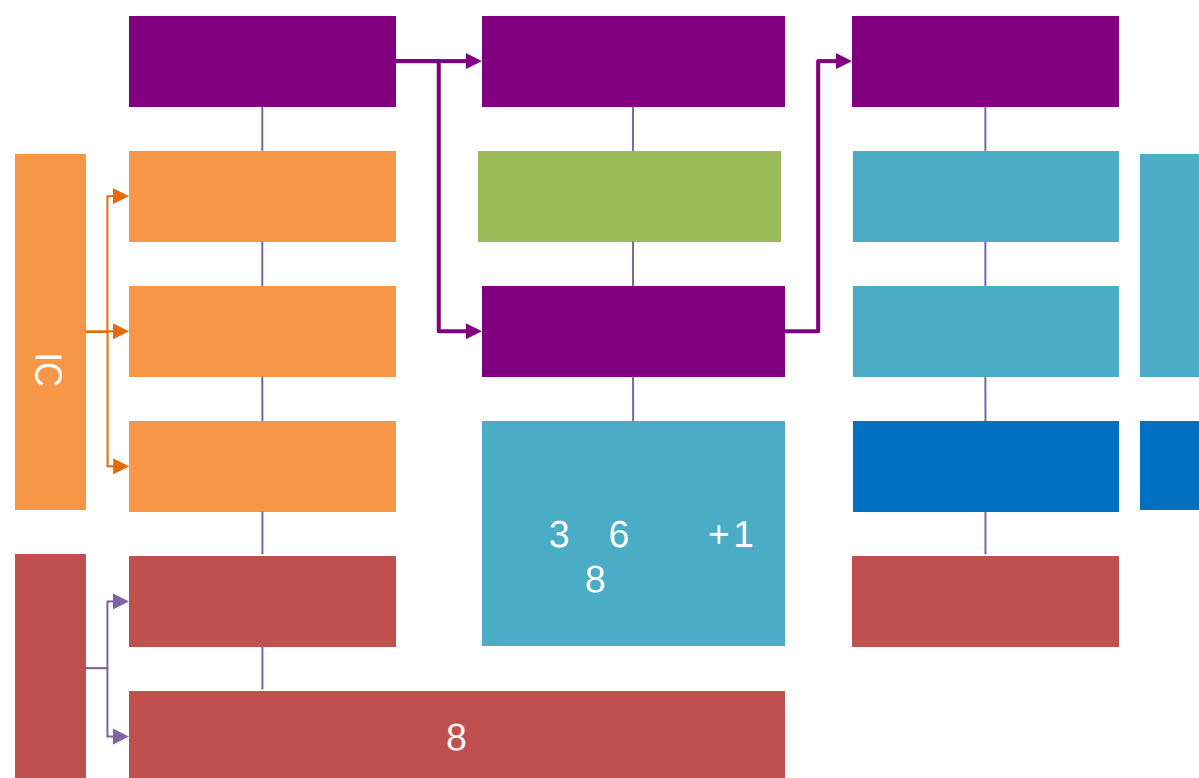
IDM

IDM

IDM



IDM

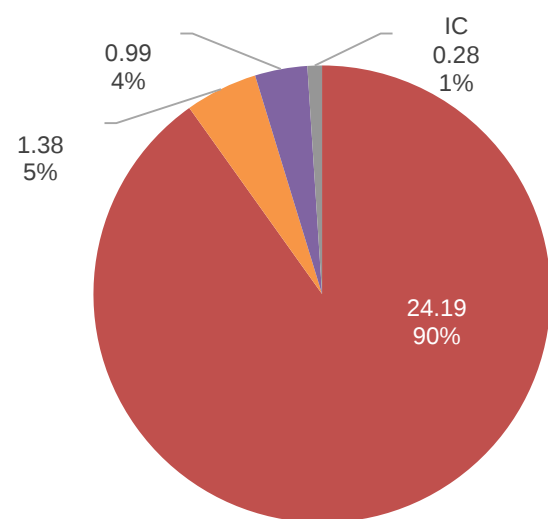


			2018
	3 6	Analog BCD MEMS DMOS Power Discrete	247
	1 8	Advance BCD Analog DMOS	

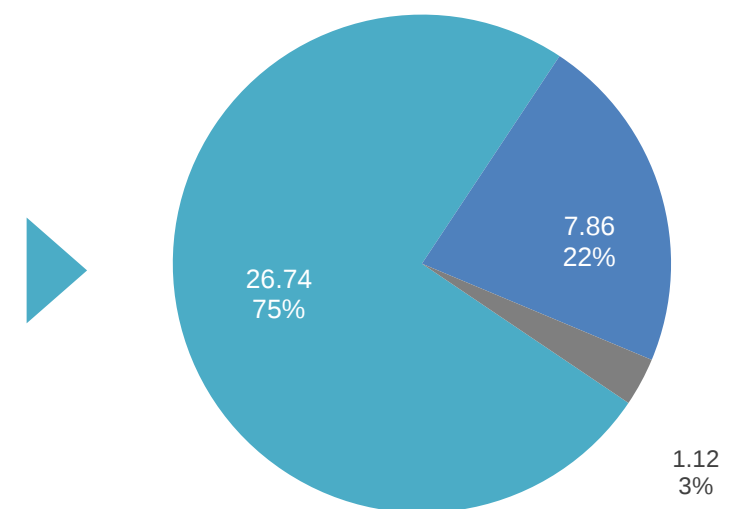
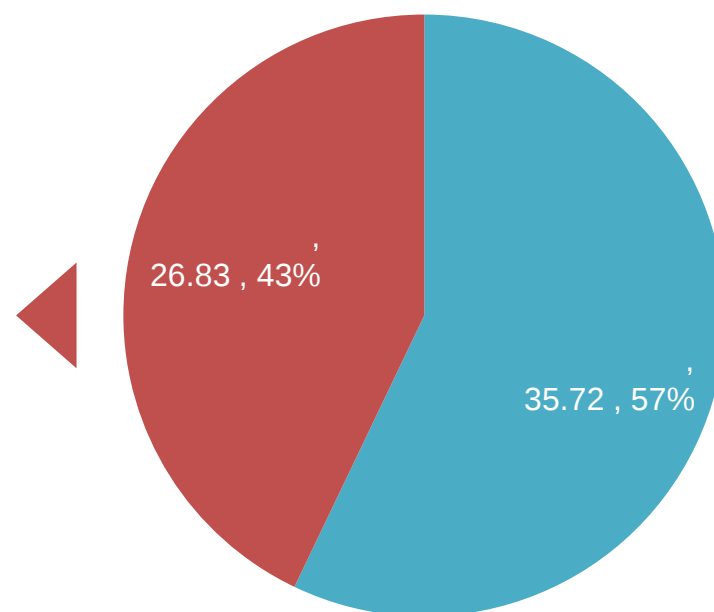
IDM

IDM
TCL MPS

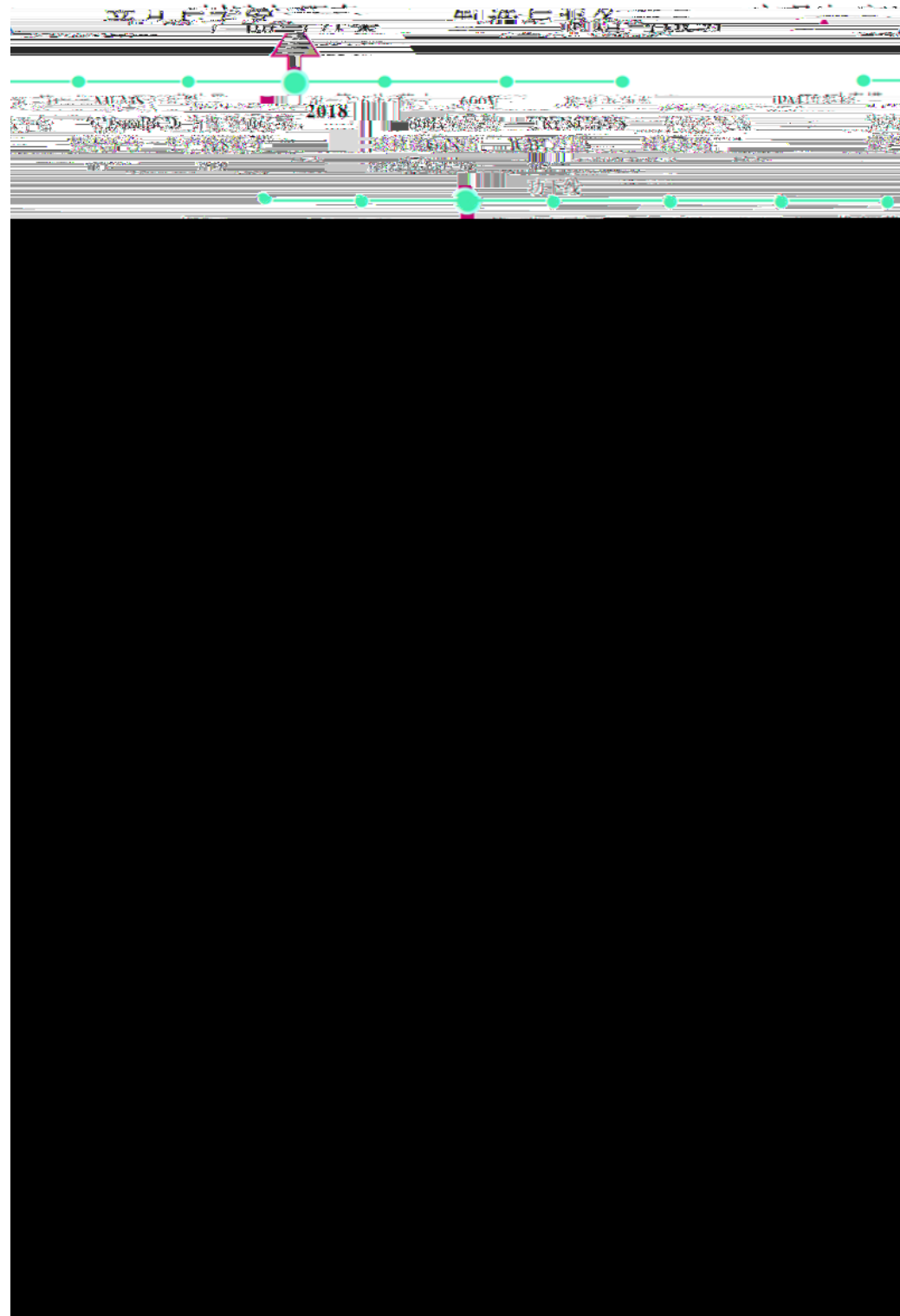
2018



wind



2008年-2018年公司关键产品与工艺发展情况



1 IDM

MOSFET

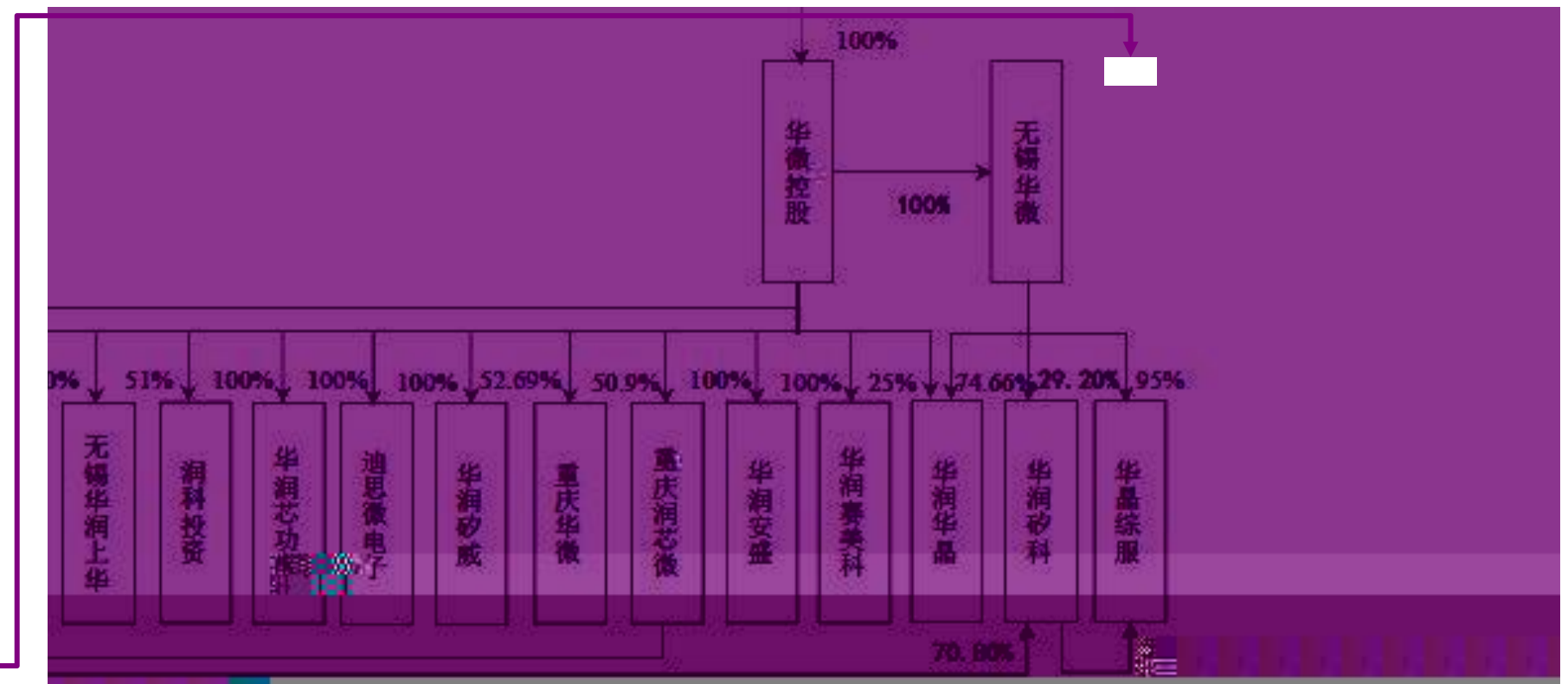
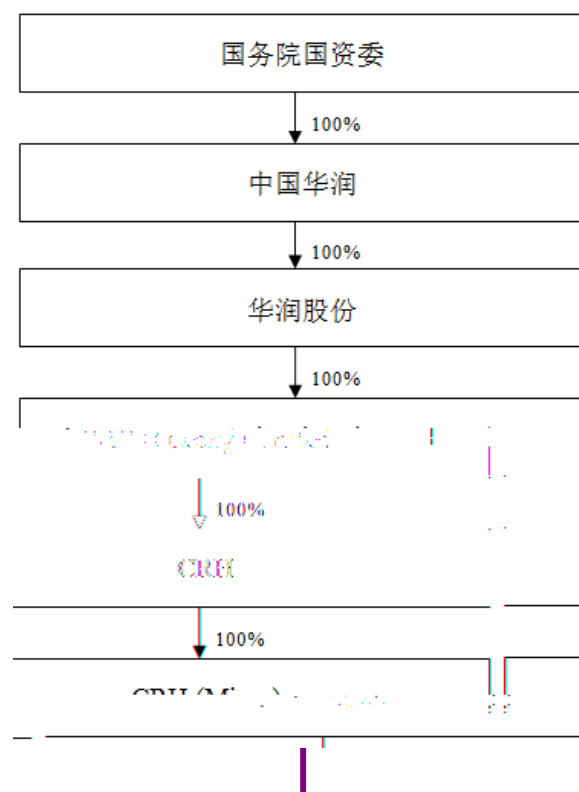
IGBT SBD FRD

1 8 3 6 1.0-0.11μm
MEMS SOI BCD CMOS CMOS Bipolar BiCMOS
GaN SiC



100%

202001



1

2

3

4

5

2

2019Q1-3	41.32	2.70
2019Q1-3	22.38%	8.58%
	4.50	36.93%

2019Q1-3

41.32

2.70

2017

2018

14.73%

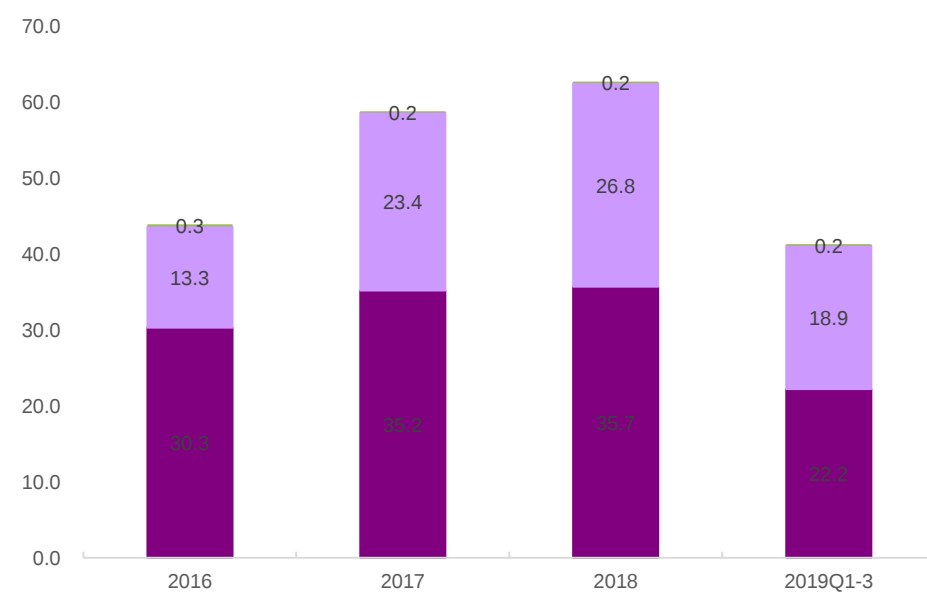
1.48%

2019H1

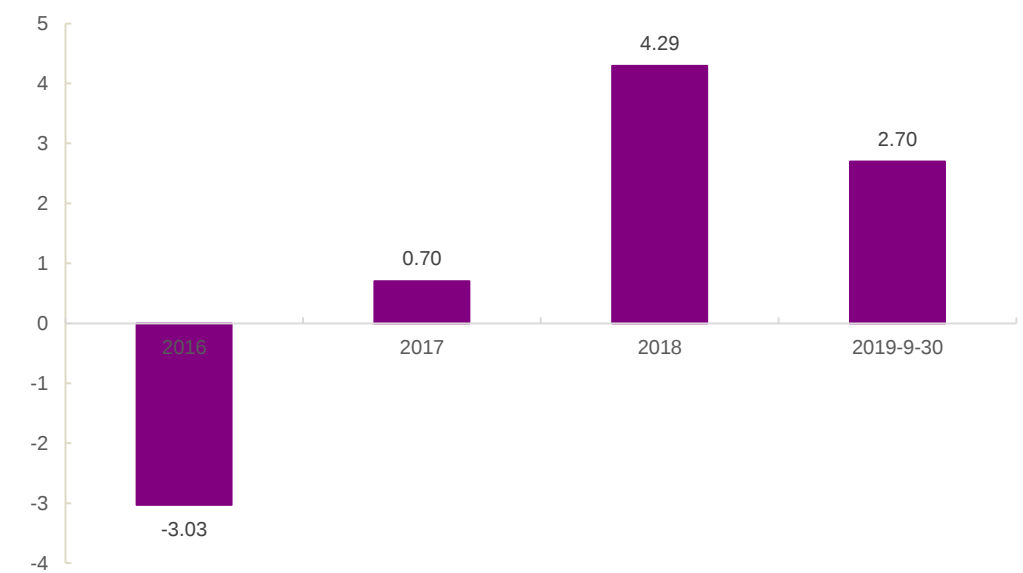
2019Q1-3

41.32

2.70



wind



wind

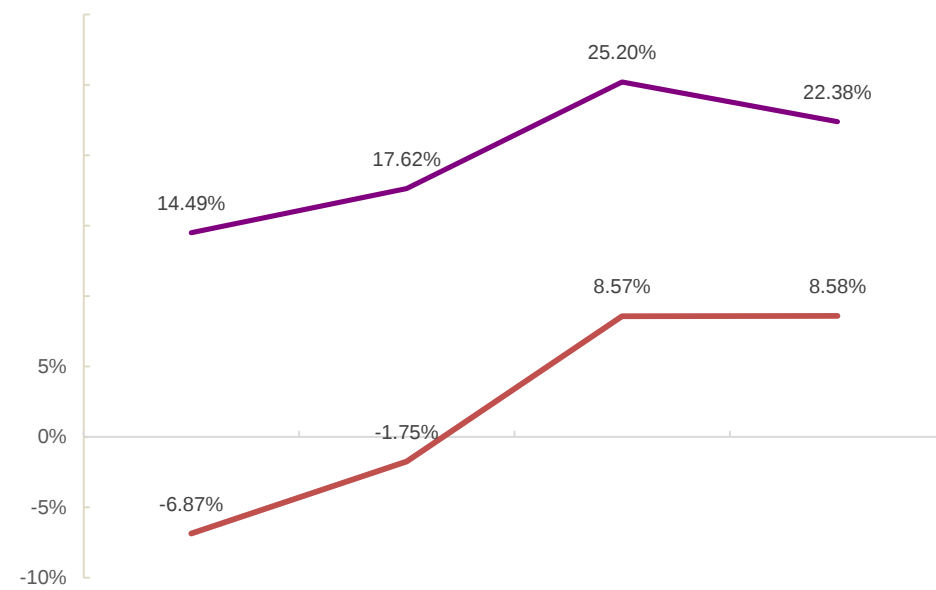
2019Q1-3

22.38%

8.58%

2018
2018

2017
2017 3.49



wind

wind





4.50

36.93%

2018

4.50

7.17%

2019

6

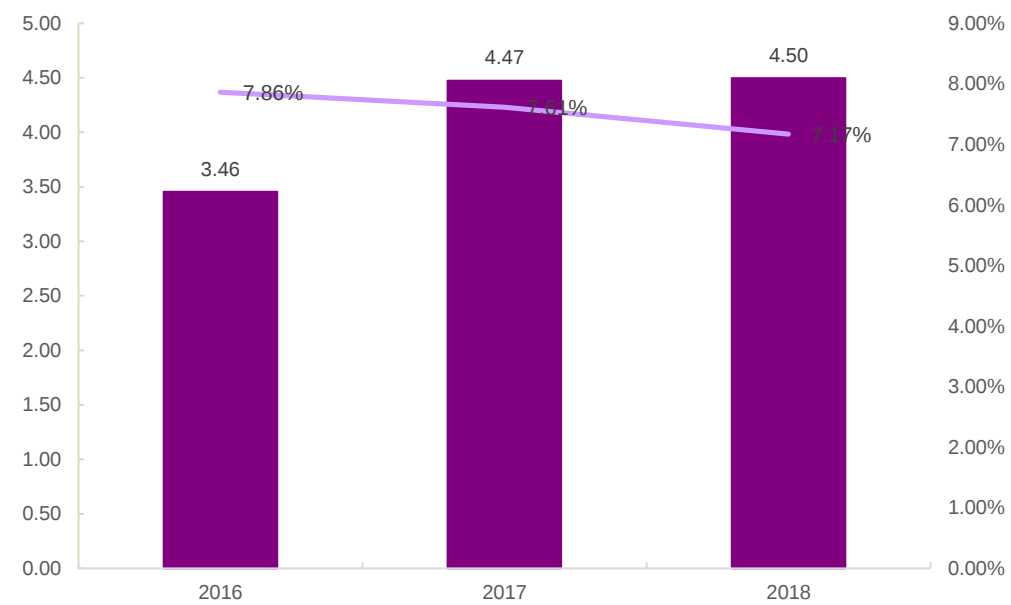
30

7,937

641

2,290

36.93%



wind





2018

80%

80%



1

2

3

4

5

3

MOEFET

$$\begin{array}{ccccccc} & & = & & + & & \text{IC} \\ 2020 & & 422 & & & & 153 & & 4\% \\ & & & & \text{MOEFET} & & & & \\ & & \text{IDM} & & & & & & \end{array}$$

= + IC

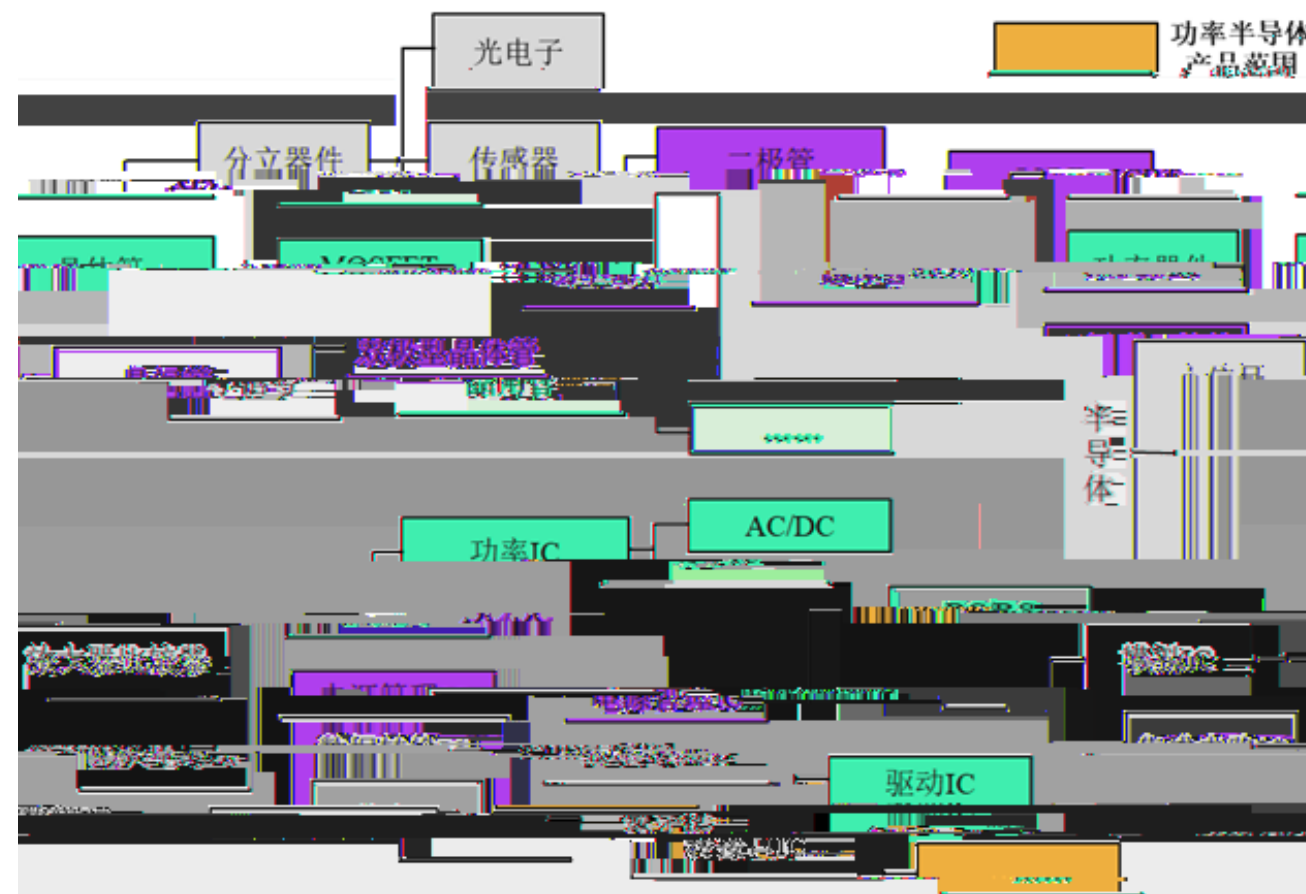
IC

IHS Markit

MOSFET IGBT

5

= + IC

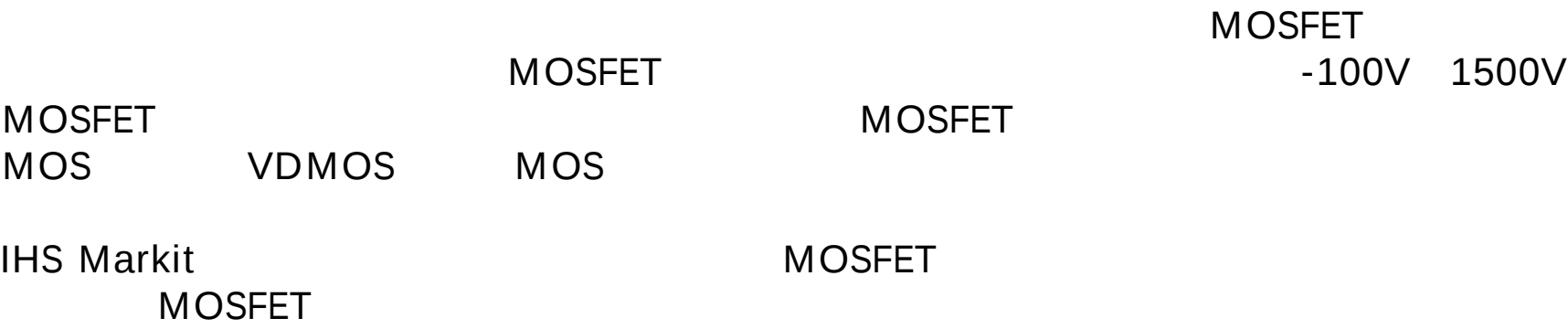




	2020	422	153	4%
IHS Markit	2018		391	2021
	441	4.1%		



MOEFET



2018

		2018 MOSFET	
1		52	28.4%
2		31	16.9%
3		16	8.7%
4		12	6.6%
5		12	6.6%
6		9	4.9%
7		51	27.9%
		183	100%

IHS Markit



IDM

2018

10

10

IDM

2018

1

2

3

4

5



8

8

8 BCD

BCD MEMS 8 MEMS 16,000

IC MEMS

50% 20% 30%

1	8	15	50%
2		6	20%
3		3	10%
4		6	20%
		30	100%



1

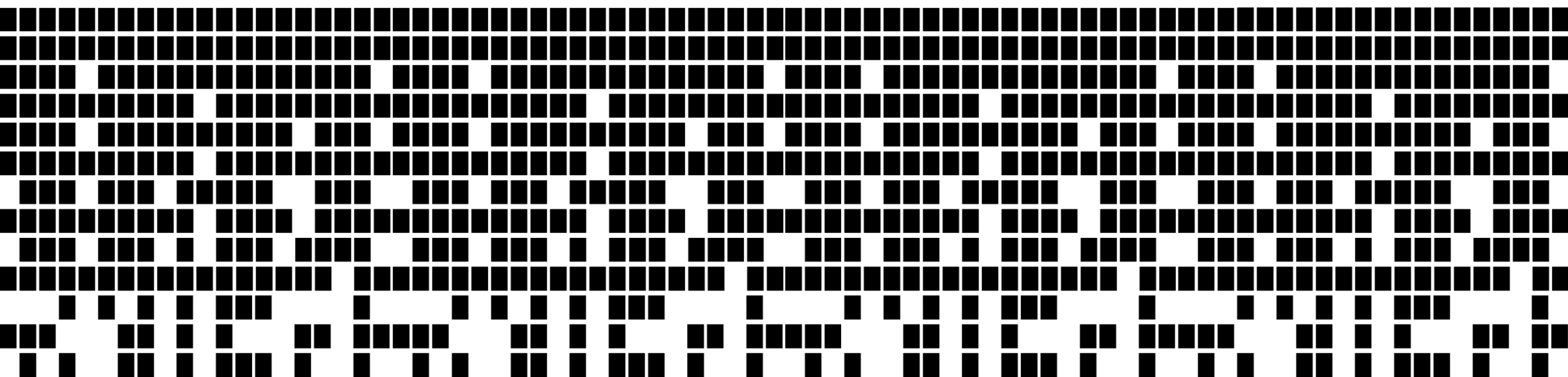
2

3

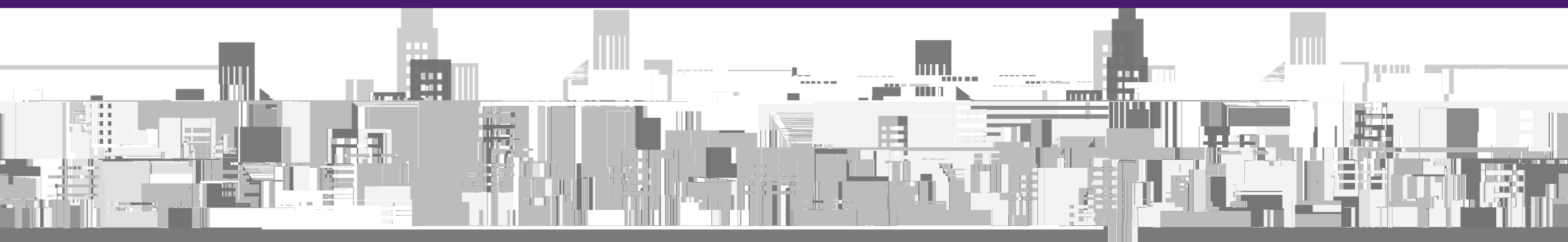
4

5





THANKYOU!



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0755-34945524

CREA VE

—	6-12	15%	
—	6-12	5%	15%
—	6-12		-5% 5%
—	6-12	5%	15%
—	6-12	15%	

A 300

“ ” 1996

“ ”